

ISOTOP[®] Boost chopper High speed Trench + Field Stop IGBT4

$V_{CES} = 1200V$

$I_{\rm C} = 40 {\rm A}$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - RBSOA and SCSOA rated
 - SiC Schottky Diode (CR1)
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
 - ISOTOP[®] Package (SOT-227)
 - Very low stray inductance
 - High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

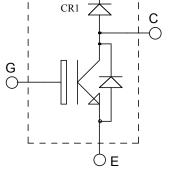
All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|------------------|---------------------------------------|------------------------|-------------|------|
| V _{CES} | Collector - Emitter Breakdown Voltage | | 1200 | V |
| т | Continuous Collector Current | $T_C = 25^{\circ}C$ | 80 | |
| I _C | Continuous Collector Current | $T_C = 80^{\circ}C$ | 40 | Α |
| I _{CM} | Pulsed Collector Current | $T_C = 25^{\circ}C$ | 160 | |
| V_{GE} | Gate – Emitter Voltage | | ± 20 | V |
| P _D | Maximum Power Dissipation | $T_C = 25^{\circ}C$ | 312 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_{j} = 150^{\circ}C$ | 80A @ 1100V | |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APT40GLQ120JCU2 - Rev 0 November, 2012







Electrical Characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|--------------------------------------|------------------------|-----|------|-----|------|
| I _{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 1200V$ | | | | 25 | μA |
| V _{CE(sat)} | Collector Emitter saturation Voltage | VGE 15 V | $T_j = 25^{\circ}C$ | 1.7 | 2.05 | 2.4 | v |
| | | | $T_{j} = 150^{\circ}C$ | | 2.6 | | v |
| V _{GE(th)} | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 1 \text{mA}$ | | 5.0 | 5.8 | 6.5 | V |
| I _{GES} | Gate – Emitter Leakage Current | $V_{GE} = \pm 20V, V_{CE} = 0V$ | | | | 120 | nA |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|------------------------|-----|------|-----|------|
| Cies | Input Capacitance | $V_{GE} = 0V$ | | | 2300 | | |
| C _{oes} | Output Capacitance | $V_{CE} = 25V$ | | | 150 | | pF |
| C _{res} | Reverse Transfer Capacitance | f = 1 MHz | | | 130 | | |
| Q _G | Gate charge | $V_{GE} = 15V, I_C = V_{CE} = 960V$ | 40A | | 185 | | nC |
| T _{d(on)} | Turn-on Delay Time | Resistive Switch | ing (25°C) | | 30 | | ns |
| T _r | Rise Time | $V_{GE} = \pm 15V$ $V_{GE} = 600V$ | | | 57 | | |
| T _{d(off)} | Turn-off Delay Time | $V_{Bus} = 600V$ $I_C = 40A$ | | | 290 | | |
| T _f | Fall Time | $R_G = 12\Omega$ | | | 16 | | |
| T _{d(on)} | Turn-on Delay Time | Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 40A$ $R_G = 12\Omega$ | | | 30 | | |
| Tr | Rise Time | | | | 49 | | ns |
| T _{d(off)} | Turn-off Delay Time | | | | 366 | | |
| $T_{\rm f}$ | Fall Time | | | | 48 | | |
| Б | Turn on Switching Energy | $V_{GE} = \pm 15V$ | $T_i = 25^{\circ}C$ | | 1.9 | | |
| Eon | Turn-on Switching Energy | $V_{Bus} = 600 V$ | $T_{i} = 150^{\circ}C$ | | 2.25 | | mJ |
| E _{off} | Turn-off Switching Energy | $I_C = 40A$ | $T_i = 25^{\circ}C$ | | 1.2 | | 1115 |
| Loff | Turn-on Switching Energy | $R_G = 12\Omega$ | $T_{i} = 150^{\circ}C$ | | 2.25 | | |
| I _{sc} | Short Circuit data | $V_{GE} \le 15V$; $V_{Bus} = 600V$ $t_p \le 10\mu s$; $T_i = 150^{\circ}C$ | | | 150 | | А |

Chopper SiC diode ratings and characteristics (CR1)

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|------------------|---|--|------------------------|------|-----|------|------|
| V _{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 1200 | | | V |
| т | Maximum Reverse Leakage Current | V _R =1200V | $T_j = 25^{\circ}C$ | | 64 | 400 | ۸ |
| I _{RM} | | | $T_{j} = 175^{\circ}C$ | | 112 | 2000 | μA |
| $I_{\rm F}$ | DC Forward Current | | $Tc = 100^{\circ}C$ | | 20 | | А |
| V _F | Diode Forward Voltage | $I_{\rm p} = 20 \Delta$ | $T_i = 25^{\circ}C$ | | 1.6 | 1.8 | V |
| ▼ F | | | $T_1 = 175^{\circ}C$ | | 2.3 | 3 | v |
| Qc | Total Capacitive Charge | $I_F = 20A, V_R = 600V$ di/dt =1000A/µs | | | 80 | | nC |
| С | Total Capacitance | $f = 1 MHz, V_R = 200 V$ | | | 192 | | pF |
| C | | $f = 1 MHz, V_R =$ | 400V | | 138 | | hr |

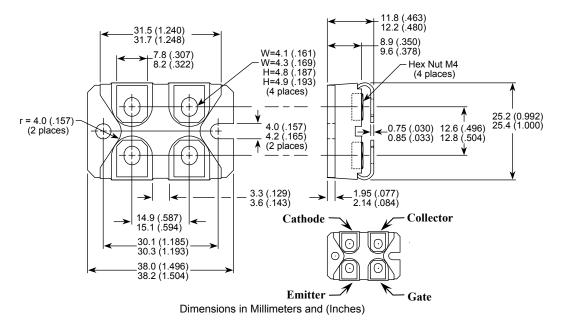
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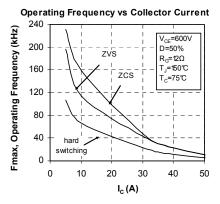
Thermal and package characteristics

| Symbol | Characteristic | | Min | Тур | Max | Unit |
|-------------------|--|-----------|------|------|------|------|
| R _{thJC} | Junction to Case Thermal Resistance | IGBT | | | 0.48 | °C/W |
| | | SiC Diode | | | 0.8 | |
| R _{thJA} | Junction to Ambient (IGBT & Diode) | | | | 20 | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | 4000 | | | V |
| T_J, T_{STG} | Storage Temperature Range | | -55 | | 150 | °C |
| $T_{\rm L}$ | Max Lead Temp for Soldering:0.063" from case for 10 sec | | | | 300 | C |
| Torque | Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine) | | | | 1.5 | N.m |
| Wt | Package Weight | | | 29.2 | | g |

SOT-227 (ISOTOP[®]) Package Outline



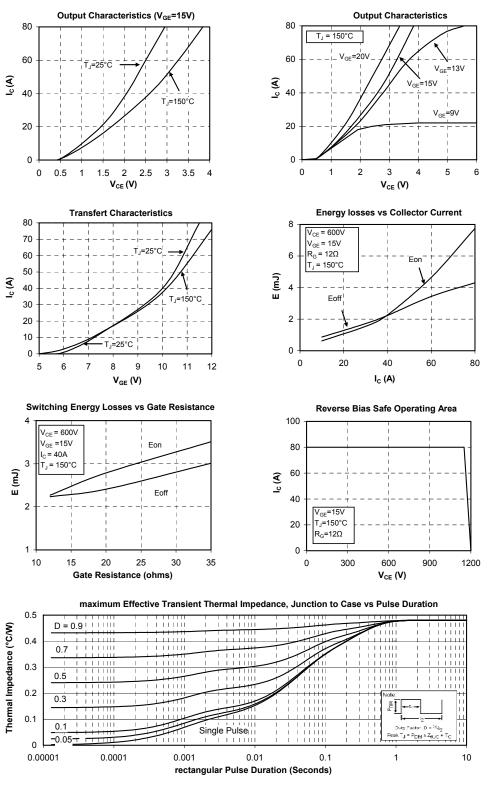
Typical IGBT Performance Curve



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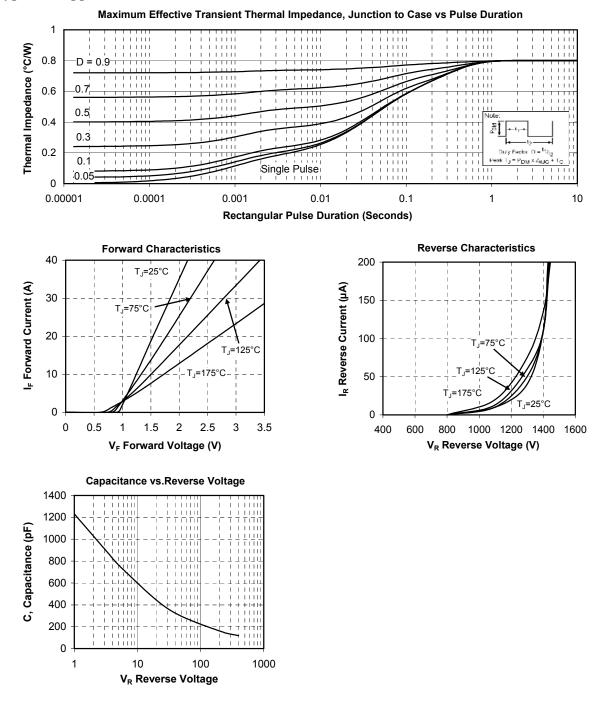


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Typical chopper SiC diode Performance Curve



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